

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property  
Organization  
International Bureau

(43) International Publication Date  
28 June 2018 (28.06.2018)



(10) International Publication Number  
**WO 2018/118210 A1**

(51) International Patent Classification:

H01L 21/822 (2006.01) H01L 27/06 (2006.01)  
H01L 21/768 (2006.01) H01L 27/092 (2006.01)  
H01L 21/8238 (2006.01)

(21) International Application Number:

PCT/US2017/058315

(22) International Filing Date:

25 October 2017 (25.10.2017)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

15/387,501 21 December 2016 (21.12.2016) US

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(81) Designated States (unless otherwise indicated, for every  
kind of national protection available): AE, AG, AL, AM,  
AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ,  
CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO,  
DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN,  
HR, HU, ID, IL, IN, IR, IS, JO, JP, KE, KG, KH, KN, KP,  
KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME,  
MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ,  
OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA,  
SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN,  
TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every  
kind of regional protection available): ARIPO (BW, GH,  
GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ,  
UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ,  
TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK,  
EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV,  
MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM,  
TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW,  
KM, ML, MR, NE, SN, TD, TG).

(54) Title: LOGIC CIRCUIT BLOCK LAYOUTS WITH DUAL-SIDED PROCESSING

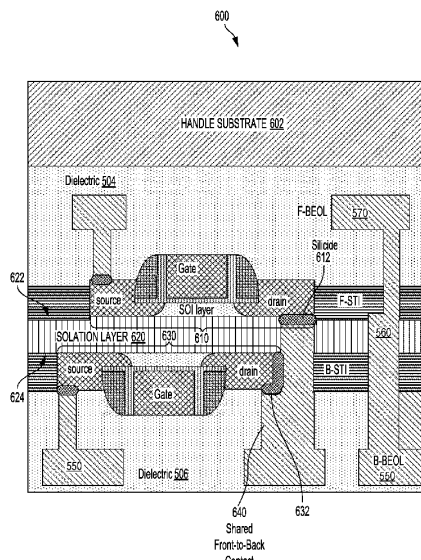


FIG. 6A

(57) Abstract: An integrated circuit device may include a p-type metal oxide semiconductor (PMOS) transistor supported by a backside of an isolation layer (620). The integrated circuit device may also include an n-type metal oxide semiconductor (NMOS) transistor supported by a front-side of the isolation layer, opposite the backside. The integrated circuit device may further include a shared contact (640) extending through the isolation layer and electrically coupling a first terminal of the PMOS transistor to the first terminal of the NMOS transistor.

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**Declarations under Rule 4.17:**

- *as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii))*
- *as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))*

**Published:**

- *with international search report (Art. 21(3))*